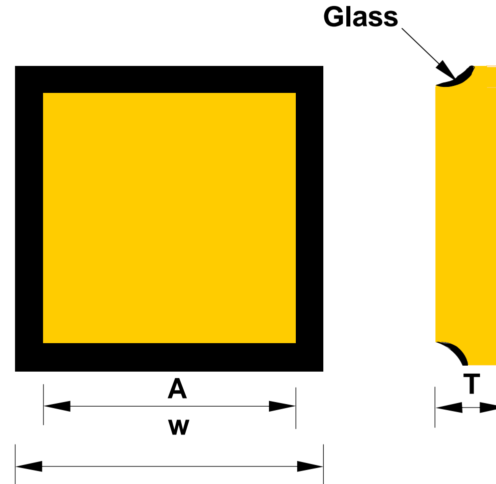
High Efficiency Rectifier GPP Chips

Features

- Fully glass passivated -needs no encapsulation
- Low forward voltage drop(V_F)
- Metallized surface



Description

The GPP chips series are diffused silicon, glass passivated rectifier die.

These devices can be supplied to meet customer's requirements.

The prime application for unencapsulated die is in hybrid circuits.

For this reason, a variety of metallized surfaces are available.

Gold is standard for wire bonding, and for soldering application, gold flash chips are supplied.

Electrical Characteristics (Ta = 25℃ unless specified)

PARAMETER	SYMBOL	HGS50					UNIT
Dimension	W	50±3					mils
Dimension	A	38±3					mils
Dimension	T	200～240					μ m
Forward current	I_F	1.0					Amps
Peak Inverse Voltage	V_B	200	400	600	800	1000	Volts
Forward Voltage Drop	V_F	1.0	1.3	1.5	1.7	1.7	Volts
Reverse Recovery Time	T_{RR}	50	50	70	75	75	ns
Reverse Current at 25℃	I_R	2	2	2	2	2	μ A
Forward Surge current	I_{FSM}	30					Amps
Junction Temperature	T_{JFM}	175					℃
Storage Temperature	T_{ST}	-65 --- 175					℃
Die attach Temperature	T_d	375					℃

Note :

Other dimension of GPP chip ranging from 42 mils to 600 mils which is not specified on the list, can also be supplied by special procurement agreement.

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